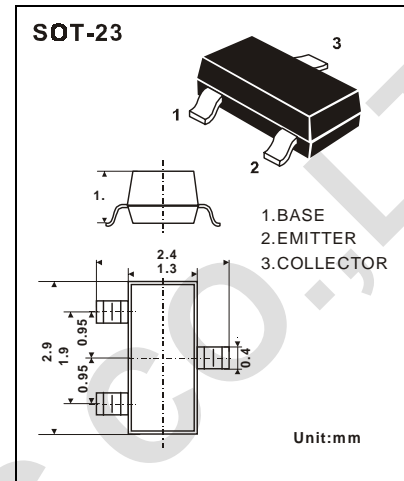


PNP EPITAXIAL SILICON TRANSISTOR

**SURFACE MOUNT SMALL
SIGNAL TRANSISTORS**

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{ceo}	-45	V
Collector-Base Voltage	V _{cbo}	-60	V
Collector Current	I _c	-800	mA
Collector Dissipation Ta=25°C*	P _D	225	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65-150	°C



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Max	Unit	Test Conditions
DC Current Gain	H _{fe}	120	400		V _{ce} = -1.0V I _c = -10mA
Collector-Emitter Saturation Voltage	V _{ce(sat)}		-1.5	V	I _c = -300mA I _b = -30mA
Gain Bandwidth Product	f _T	100		MHz	V _{ce} = -5V I _c = -10mA f = 50MHz

* Total Device Dissipation : FR=1x0.75x0.062in Board, Derate 25°C.

Pulse Test: Pulse Width ≤ 300uS, Duty cycle ≤ 2%